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wherein the conductive die-bonding paste adheres to a lower part of each end surface of the chip, and a highest position of the conductive die-bonding paste on said lower part of each end surface of the semiconductor laser chip is at a height of more than 0.01 mm from the bonding surface and hence from the bottom of the semiconductor laser chip, but is below the light-emitting point of the semiconductor laser chip of the semiconductor laser apparatus.

13. (Amended) A semiconductor laser apparatus comprising:

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a semiconductor laser chip die-bonded to a bonding surface with a conductive die-bonding paste, said semiconductor laser chip having a light-emitting point at at least one end surface thereof so as to provide a semiconductor laser apparatus,

wherein a highest position at which the conductive die-bonding paste adheres to at least one end surface of the semiconductor laser chip is at a height of more than 0.01 mm from the bonding surface, but is below the light-emitting point of the semiconductor laser chip; and

wherein the conductive die-bonding paste comprises epoxy resin and at least 80% by weight conductive filler of metal particles or flakes.

14. (Amended) A semiconductor laser apparatus for use in an optical pickup using a three-beam scheme for optical disks, the semiconductor laser apparatus comprising: